

N-Channel 30 V (D-S) Super Junction MOSFET

| PRODUCT SUMMARY | | | | | | |
|---------------------|----------------------------------|---------------------------------|-----------------------|--|--|--|
| V _{DS} (V) | $R_{DS(on)}$ (m Ω)(Typ.) | I _D (A) ^a | Q _g (Typ.) | | | |
| 30 | 0.88 at V _{GS} = 10 V | 240 | F0 ~C | | | |
| 30 | 1.9 at V _{GS} = 4.5 V | 210 | 52 nC | | | |

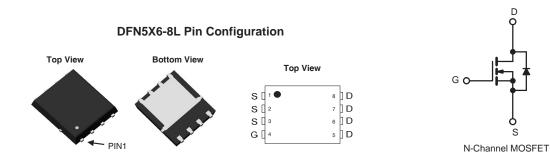
FEATURES

- DT-SJ Power MOSFET
- 100 % R_q and UIS Tested



APPLICATIONS

- · Li- Battery Protection
- Motor Drive
- Power Managment for High Performance Application



| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | | | | |
|--|-------------------------|-----------------------------------|--------------------|----|--|--|
| Parameter | Symbol | Limit | Unit | | | |
| Drain-Source Voltage | | V _{DS} | 30 | V | | |
| Gate-Source Voltage | | V _{GS} | ± 20 | V | | |
| Continuous Drain Current (T _{.1} = 150 °C) | T _C = 25 °C | I _D | 210 | А | | |
| Continuodo Brain Carrent (1) = 100 O) | T _C = 100 °C | טי | 127 | | | |
| Pulsed Drain Current | | I _{DM} | 840 | | | |
| Single-Pulse Avalanche Energy | | E _{AS} | 387 | mJ | | |
| | T _C = 25 °C | | 188 | W | | |
| Maximum Power Dissipation | T _C = 100 °C | P _D | 120 | | | |
| Maximum Fower Dissipation | T _A = 25 °C | ם י ט | 5.8 ^{b,c} | | | |
| | T _A = 100 °C | | 3.7 ^{b,c} | | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| Maximum Junction-to-Ambient ^b | t ≤ 10 s | R_{thJA} | 15 | 22 | °C/W | |
| Maximum Junction-to-Case | Steady State | R _{thJC} | 0.5 | 0.66 | C/VV | |

- a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.
- c. t = 10 s.



| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
|---|---------------------|--|------|------|-------|------|--|
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0, I_D = 250 \mu\text{A}$ | 30 | | | V | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ | 1 | | 3 | V | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | | | ± 100 | nA | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 30 V, V _{GS} = 0 V | | | 1 | | |
| Zero Gate Voltage Drain Gurrent | | V _{DS} = 30 V, V _{GS} = 0 V, T _J = 125 °C | | | 100 | μA | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 210 | | | Α | |
| | В | V _{GS} = 10 V, I _D = 20 A | | 0.88 | 1.05 | 0 | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 4.5 V, I _D = 20 A | | 1.9 | 2.6 | mΩ | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = 5 V,I _D = 20 A | | 90 | | S | |
| Dynamic ^b | | | | | | | |
| Input Capacitance | C _{iss} | | | 2993 | | | |
| Output Capacitance | C _{oss} | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 2038 | | pF | |
| Reverse Transfer Capacitance | C _{rss} | 1 | | 75 | | | |
| Total Gate Charge | Q_g | | | 52 | | | |
| Gate-Source Charge | Q_{gs} | V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A | | 7.2 | | nC | |
| Gate-Drain Charge | Q_{gd} | 1 | | 11 | | | |
| Gate Resistance | R _g | f = 1 MHz | | 1.8 | | Ω | |
| Turn-On Delay Time | t _{d(on)} | | | 7 | | | |
| Rise Time | t _r | $V_{DD} = 15 \text{ V, R}_{L} = 0.5 \Omega$ | | 29 | | 1 | |
| Turn-Off DelayTime | t _{d(off)} | $I_D \cong 20 \text{ A, V }_{GEN} = 10 \text{ V, R }_{g} = 3 \Omega$ | | 35 | | - ns | |
| Fall Time | t _f | 1 | | 22 | | = | |
| Drain-Source Body Diode Characteris | tics | | | | | | |
| Continous Source-Drain Diode Current | I _S | T _C = 25 °C | | | 210 | Α | |
| Pulse Diode Forward Current (100 μs) | I _{SM} | | | | 840 | | |
| Body Diode Voltage | V _{SD} | I _S = 1 A | | | 1.2 | V | |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 20 A, dl/dt = 100 A/µs, T ₁ = 25 °C | | 47 | | ns | |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | 55 | | nC | |

Notes:

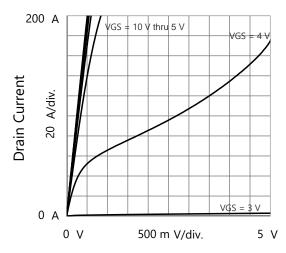
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

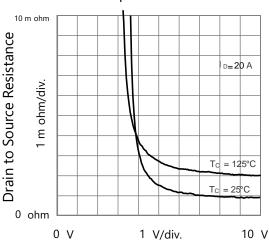
b. Guaranteed by design, not subject to production testing.



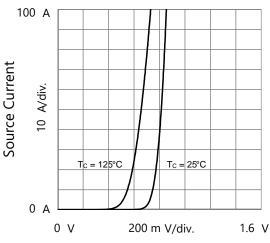
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



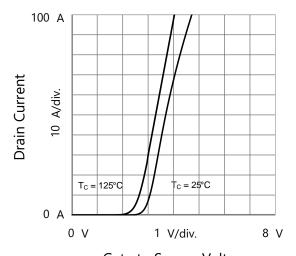
Drain to Source Voltage Output Characteristics



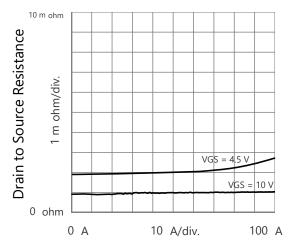
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



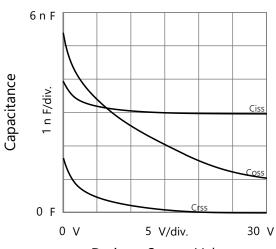
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



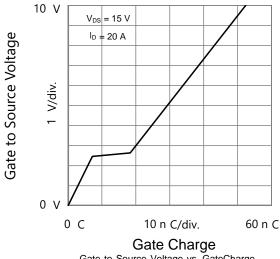
Drain Current
Drain to Source Resistance vs. Drain Current



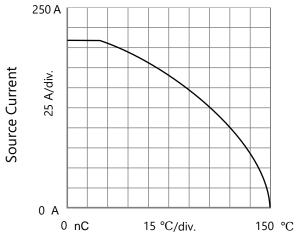
Drain to Source Voltage Capacitances



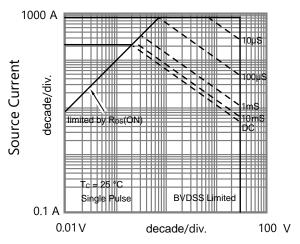
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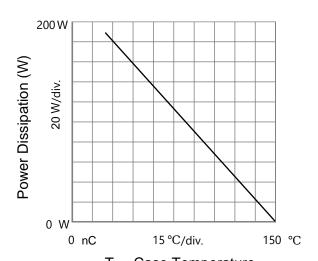




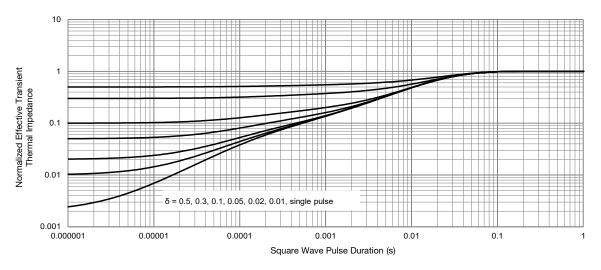
T_C - Case Temperature



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T_C - Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case

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